

@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage	V _{DSS}	40	V		
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note C) / - 40V	Steady State	T _A = +25°C T _A = +70°C	I _D	14.4 11.6	А
Continuous Drain Current (Note 6) V _{GS} = 10V	t<10s	T _A = +25°C T _A = +70°C	I _D	19.2 15.4	А
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I _{DM}	90	Α		
Maximum Continuous Body Diode Forward Current (Note 6)			I _S	3	Α
Avalanche Current, L = 0.1mH			I _{AS}	38	Α
Avalanche Energy, L = 0.1mH			E _{AS}	75	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

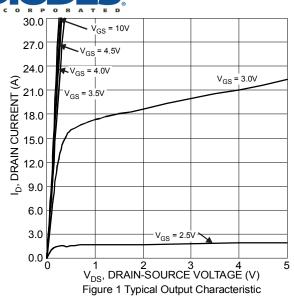
Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)		P_{D}	1.0	W
Thermal Decistores, Junction to Ambient (Note 5)	Steady state	0	119	°C/W
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	$R_{\theta JA}$	66	
Total Power Dissipation (Note 6)		P_{D}	2.3	W
Thermal Desistance, Junction to Ambient (Note C)	Steady state		53	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	$R_{\theta JA}$	30	
Thermal Resistance, Junction to Case (Note 6)		R _{eJC}	6.1	
Operating and Storage Temperature Range		$T_{J,} T_{STG}$	-55 to +150	°C

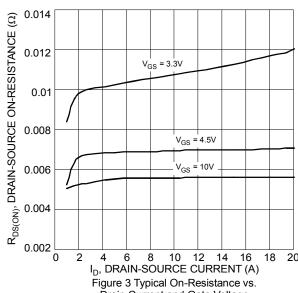
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

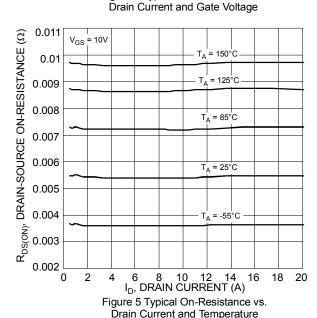
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	40	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}		_	1	μΑ	$V_{DS} = 40V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}		_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(th)}	1	_	3	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
			5.5	7.5	mΩ	$V_{GS} = 10V, I_D = 10A$	
Static Drain-Source On-Resistance	R _{DS (ON)}		7	10		$V_{GS} = 4.5V, I_D = 8A$	
	, ,	_	_	20		$V_{GS} = 3.3V, I_D = 6A$	
Diode Forward Voltage	V_{SD}		0.7	1.1	V	V _{GS} = 0V, I _S = 1A	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}		3537		рF	.,	
Output Capacitance	Coss	_	257	_	pF	V _{DS} = 20V, V _{GS} = 0V, -f = 1MHz	
Reverse Transfer Capacitance	C _{rss}	_	215	_	pF	I - IIVIHZ	
Gate Resistance	R_g	_	0.9	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	34	_	nC		
Total Gate Charge (V _{GS} = 10V)	Q_g	_	74	_	nC	\\ - 20\\ \ \ - 40A	
Gate-Source Charge	Q _{gs}	_	10.2	_	nC	$V_{DS} = 20V, I_{D} = 10A$	
Gate-Drain Charge	Q_{gd}	_	12.5	_	nC	7	
Turn-On Delay Time	t _{D(on)}		8.2	_	ns		
Turn-On Rise Time	t _r		14.1	_	ns	V _{GS} = 10V, V _{DS} = 20V,	
Turn-Off Delay Time	t _{D(off)}		69.7	_	ns	$R_G = 6\Omega$, $I_D = 10A$	
Turn-Off Fall Time	t _f		24.4	_	ns	1	
Body Diode Reverse Recovery Time	t _{rr}	_	18.5	_	nS	-I _F = 10A, di/dt = 100A/μs	
Body Diode Reverse Recovery Charge	Q _{rr}		12.0		nC		

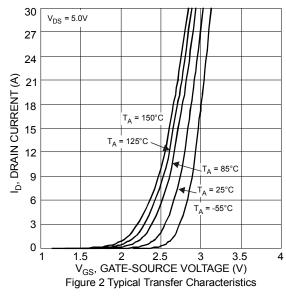
Notes:

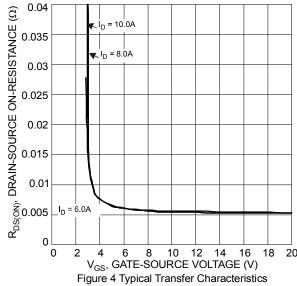
- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate
 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to product testing.











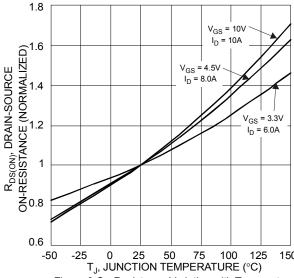
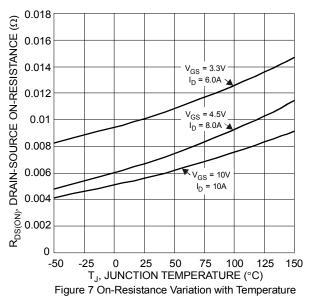
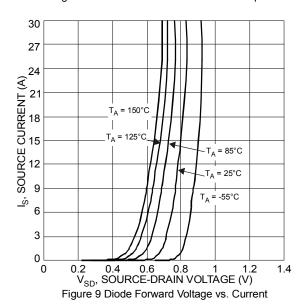
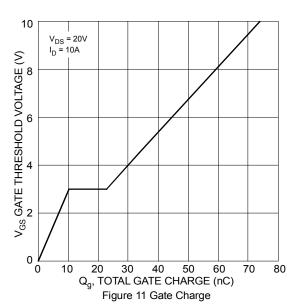


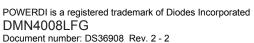
Figure 6 On-Resistance Variation with Temperature

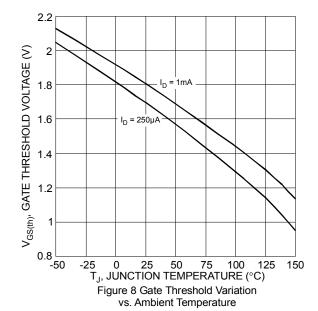


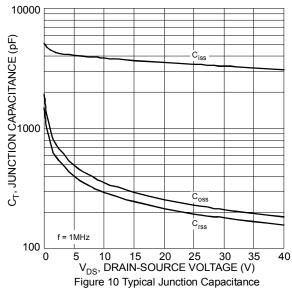


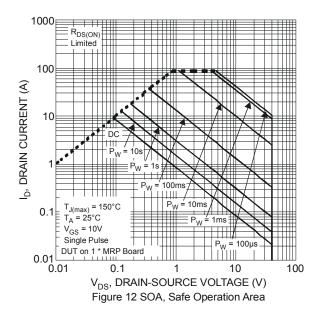




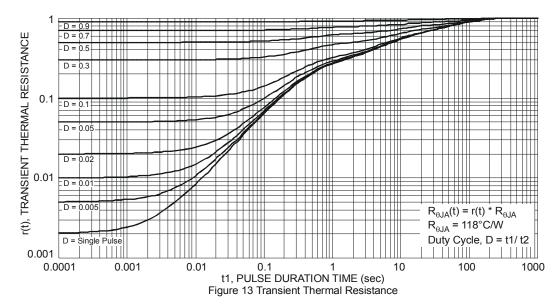






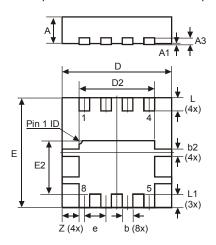






Package Outline Dimensions

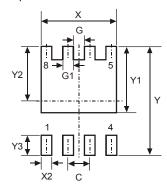
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



POWERDI®3333-8					
Dim	Min	Max	Тур		
D	3.25	3.35	3.30		
Е	3.25	3.35	3.30		
D2	2.22	2.32	2.27		
E2	1.56	1.66	1.61		
Α	0.75	0.85	0.80		
A1	0	0.05	0.02		
A3	_	_	0.203		
b	0.27	0.37	0.32		
b2	_	-	0.20		
L	0.35	0.45	0.40		
L1	_	_	0.39		
е	_	_	0.65		
Z	_	_	0.515		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	0.650
G	0.230
G1	0.420
Υ	3.700
Y1	2.250
Y2	1.850
Y3	0.700
Х	2.370
X2	0.420

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